

PMR280UN

N-channel TrenchMOS ultra low level FET Rev. 2 — 3 February 2012

Product data sheet

Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in ultra small Surface-Mounted Device (SMD) plastic package using TrenchMOS technology.

1.2 Features and benefits

- Surface mounted package
- Low on-state resistance

- Footprint 63% smaller than SOT23
- Low threshold voltage

1.3 Applications

Driver circuits

Switching in portable appliances

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	-	20	V
I _D	drain current	$T_{sp} = 25 ^{\circ}C; V_{GS} = 4.5 V$	-	-	0.98	Α
V_{GS}	gate-source voltage		-8	-	8	V
Static chara	Static characteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 0.2 \text{ A}; T_j = 25 \text{ °C}$	-	280	340	mΩ

Pinning information 2.

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		5
2	S	source	3	
3	D	drain	1 2	G S
			SOT416 (SC-75)	017aaa253



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3. Ordering information

Table 3. Ordering information

Type number Package			
	Name	Description	Version
PMR280UN	SC-75	plastic surface-mounted package; 3 leads	SOT416

4. Marking

Table 4. Marking codes

Type number	Marking code
PMR280UN	R5

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	20	V
V_{DGR}	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 150$ °C; $R_{GS} = 20$ kΩ	-	20	V
V_{GS}	gate-source voltage		-8	8	V
I _D	drain current	$T_{sp} = 25 ^{\circ}\text{C}; V_{GS} = 4.5 \text{V}$	-	0.98	Α
		$T_{sp} = 100 ^{\circ}\text{C}; V_{GS} = 4.5 \text{V}$	-	0.62	Α
I _{DM}	peak drain current	T_{sp} = 25 °C; pulsed; $t_p \le 10 \mu s$	-	1.97	Α
P _{tot}	total power dissipation	T _{sp} = 25 °C	-	0.53	W
T _{stg}	storage temperature		-55	150	°C
Tj	junction temperature		-55	150	°C
Source-drain	diode				
Is	source current	T _{sp} = 25 °C	-	0.44	Α
I _{SM}	peak source current	$T_{sp} = 25$ °C; pulsed; $t_p \le 10 \mu s$	-	0.88	Α

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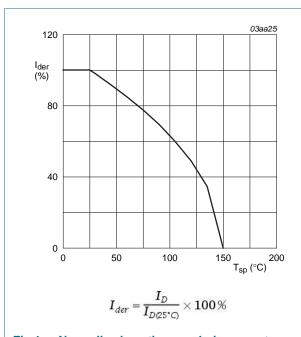


Fig 1. Normalized continuous drain current as a function of mounting base temperature

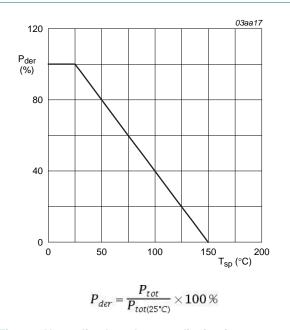


Fig 2. Normalized total power dissipation as a function of solder point temperature

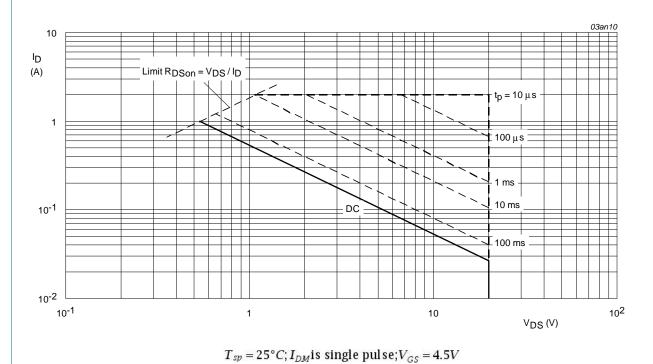


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	235	K/W

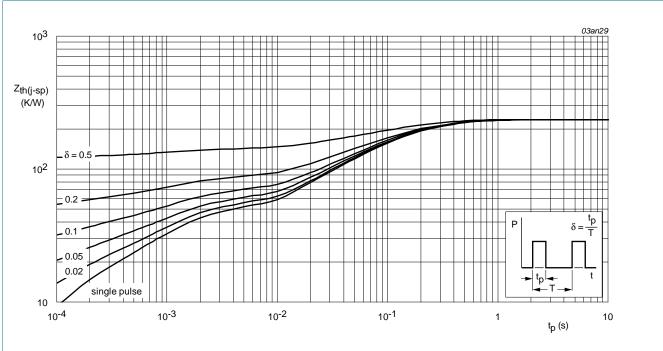


Fig 4. Transient thermal impedance from junction to solder point as a function of pulse duration

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7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source	$I_D = 1 \mu A; V_{GS} = 0 V; T_j = 25 °C$	20	-	-	V
	breakdown voltage	$I_D = 1 \mu A; V_{GS} = 0 V; T_j = -55 °C$	18	-	-	V
$V_{GS(th)}$	gate-source threshold	$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.45	0.7	1	V
	voltage	$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.25	-	-	V
		$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	1.2	V
I _{DSS}	drain leakage current	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
R _{DSon}	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 0.2 \text{ A}; T_j = 25 \text{ °C}$	-	280	340	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 0.2 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	448	544	mΩ
		$V_{GS} = 2.5 \text{ V}; I_D = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	360	430	mΩ
		$V_{GS} = 1.8 \text{ V}; I_D = 0.075 \text{ A}; T_j = 25 \text{ °C}$	-	460	660	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 1 \text{ A}; V_{DS} = 10 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	0.89	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.13	-	nC
Q_{GD}	gate-drain charge		-	0.18	-	nC
C _{iss}	input capacitance	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	45	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	11	-	pF
C _{rss}	reverse transfer capacitance		-	7	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 10 V; R_L = 10 Ω ; V_{GS} = 4.5 V;	-	4.5	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	10	-	ns
t _{d(off)}	turn-off delay time		-	18.5	-	ns
t _f	fall time		-	5	-	ns
Source-d	rain diode					
V _{SD}	source-drain voltage	$I_S = 0.3 \text{ A}; V_{GS} = 0 \text{ V}; T_i = 25 ^{\circ}\text{C}$	-	0.83	1.2	V

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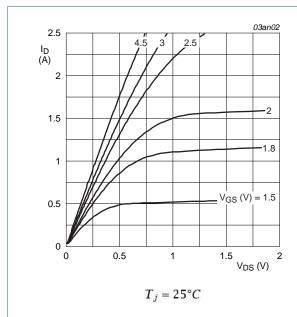


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

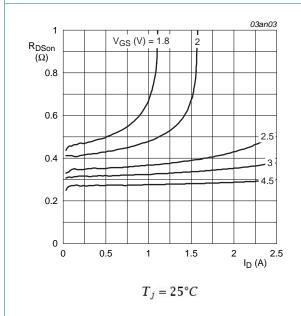
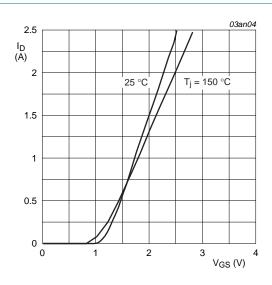


Fig 7. Drain-source on-state resistance as a function of drain current; typical values



 $T_j = 25^{\circ}C$ and $150^{\circ}C$; $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

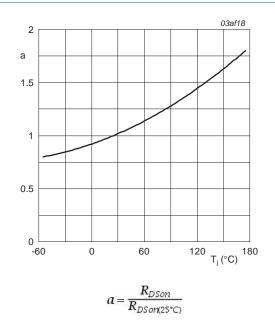


Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature

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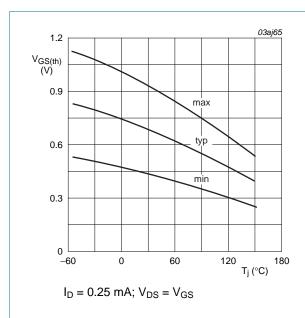
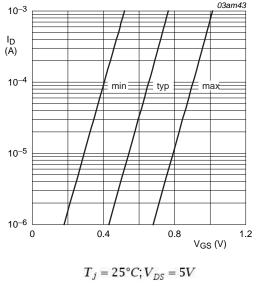


Fig 9. Gate-source threshold voltage as a function of junction temperature



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Fig 10. Sub-threshold drain current as a function of gate-source voltage

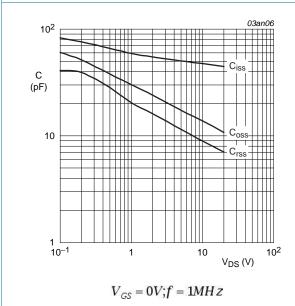
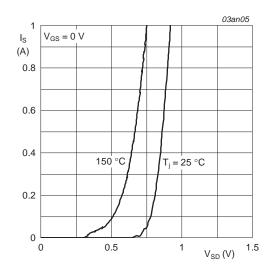


Fig 11. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $T_j = 25^{\circ} C$ and $150^{\circ} C$; $V_{GS} = 0V$

Fig 12. Source current as a function of source-drain voltage; typical values

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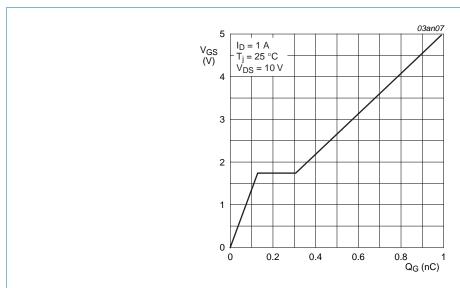
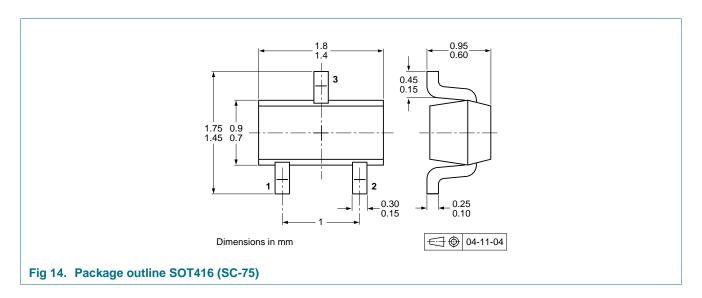


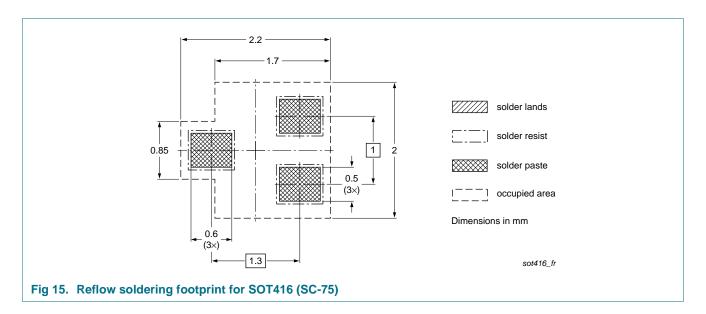
Fig 13. Gate-source voltage as a function of gate charge; typical values

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8. Package outline



9. Soldering



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10. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMR280UN v.2	20120203	Product data sheet	-	PMR280UN v.1
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines NXP Semiconductors. 			
	 Legal texts have 	ve been adapted to the new	company name where	appropriate.
PMR280UN v.1	20040305	Product data sheet	-	-

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11.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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